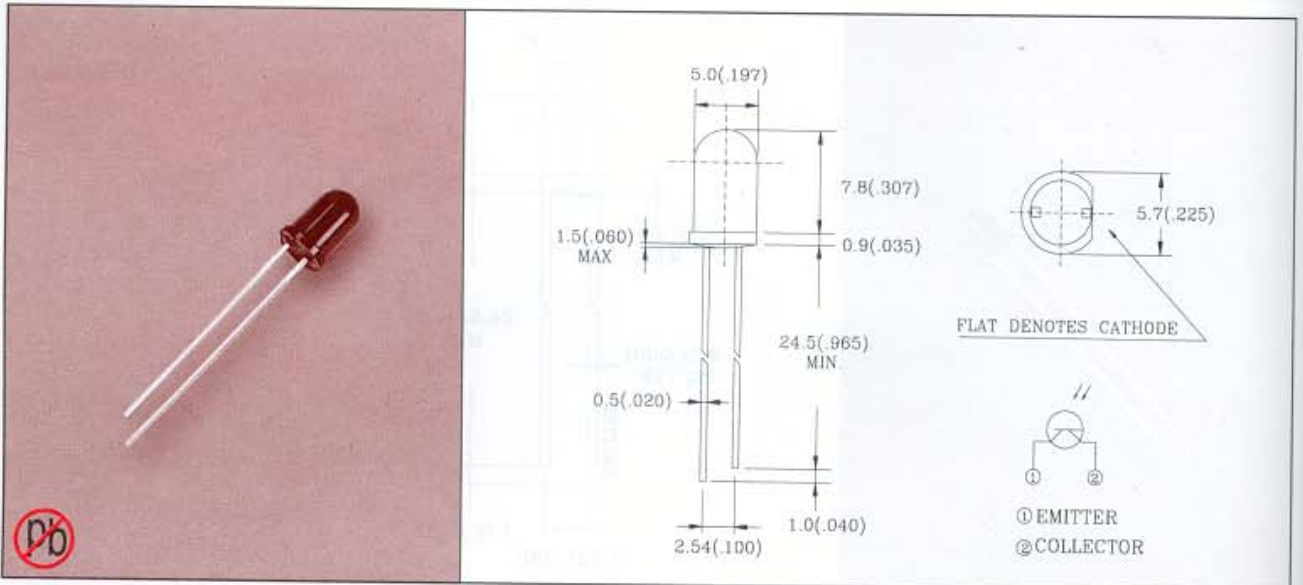


**L-51ROPT1XX 5.0mm PHOTOTRANSISTOR**



◆ **ABSOLUTE MAXIMUM RATING:(Ta=25°C)**

Part No.	P <sub>D</sub> (mw)	V <sub>(BR)R</sub> (V)	Topr	Tstg
L-51ROPT1XX	10	5	-35°C to 85°C	-35°C to 85°C
<b>PARAMETER</b>	<b>Power Dissipation</b>	<b>Reverse break down voltage</b>	<b>Operating Temperature Range</b>	<b>Storage Temperature Range</b>
<b>Lead Soldering Temperature {1.6mm(0.063 inch)From Body}250°C ±5°C For 3 Seconds</b>				

◆ **ELECTRO-OPTICAL CHARACTERISTICS:(Ta=25°C)**

Part No.	BV <sub>CEO</sub> (V)			BV <sub>ECO</sub> (V)			I <sub>CEO</sub> (nA)			V <sub>CE(s)</sub> (V)			t <sub>r</sub> /t <sub>f</sub> (uS)			I <sub>c</sub> (mA)			C <sub>CB</sub> (pF)			λ (nm)				
	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	PEAK	MAX		
L-51ROPT1C	30			5					100			0.4	15/15			1.8	2.4			6.4			400		1050	
L-51ROPT1D1	30			5					100			0.4	15/15			1.7	2.2			6.4			900		940	
L-51ROPT1D2	30			5					100			0.4	15/15			1.7	2.2			6.4			800		870	
<b>TEST CONDITION</b>	I <sub>C</sub> =100uA E <sub>e</sub> =0mW/cm <sup>2</sup>			I <sub>E</sub> =100uA E <sub>e</sub> =0mW/cm <sup>2</sup>			V <sub>E</sub> =10V E <sub>e</sub> =0mW/cm <sup>2</sup>			I <sub>C</sub> =2mA E <sub>e</sub> =0.5mW/cm <sup>2</sup>			V <sub>CE</sub> =5V I <sub>C</sub> =1mA R <sub>L</sub> =1000Ω			V <sub>CE</sub> =5V E <sub>e</sub> =0.1mW/cm <sup>2</sup>			f=1MHZ V <sub>CB</sub> =3V E <sub>e</sub> =0mW/cm <sup>2</sup>							
<b>PARAMETER</b>	<b>COLLECTOR-EMITTER BREAKDOWN VOLTAGE</b>			<b>EMITTER-COLLECTOR BREAKDOWN VOLTAGE</b>			<b>COLLECTOR DARK CURRENT</b>			<b>COLLECTOR-EMITTER SATURATION VOLTAGE</b>			<b>RISE/FALL TIME</b>			<b>ON STATE COLLECTOR CURRENT</b>			<b>COLLECTOR -BASE CAPACITANCE</b>			<b>SPECTRAL SENSITIVITY WAVELENGTH</b>				

- 1.All dimension are in millimeters (inches).
- 2.Tolerance is ± 0.25 mm (0.01") unless otherwise specified.
- 3.Reference only. Check engineering data sheet for further confirmation.